

Product Summary

BV _{DSS}	Max R _{DS(ON)}	Max I _D @ T _A = +25°C
-30V	1Ω @ V _{GS} = -4.5V	-0.76A
	1.5Ω @ V _{GS} = -2.5V	-0.62A
	2Ω @ V _{GS} = -1.8V	-0.54A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

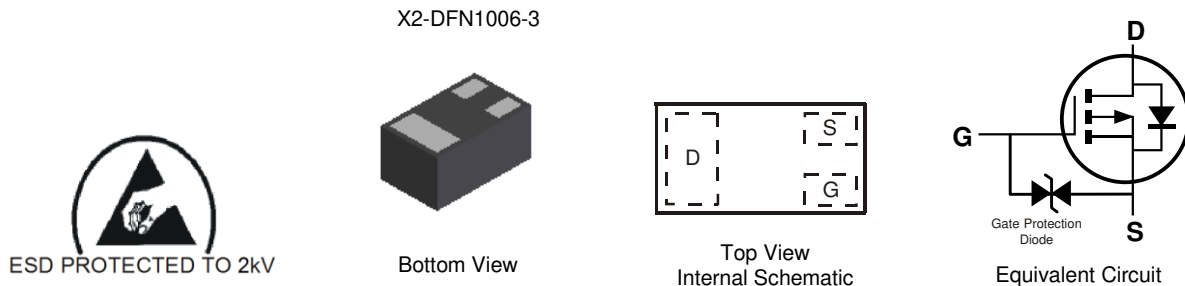
- Load Switch in portable electronics

Features and Benefits

- Footprint of just 0.6mm² – Thirteen Times Smaller than SOT23
- 0.4mm Profile – Ideal for Low Profile Applications
- Low Gate Threshold Voltage
- Fast Switching Speed
- ESD Protected Gate 2KV
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 **e4**
- Terminal Connections: See Diagram
- Weight: 0.001 grams (Approximate)



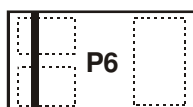
Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DMP31D0UFB4-7B	P6	7	8	10,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information

DMP31D0UFB4-7B



P6 = Product Type Marking Code

Top View
Bar Denotes Gate
And Source Side

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current	Steady State	T _A = +25°C (Note 6)	I _D	-0.76	A
		T _A = +85°C (Note 6)		-0.55	
		T _A = +25°C (Note 5)		-0.54	
Pulsed Drain Current (Note 7)			I _{DM}	2	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P _D	0.46	W
	(Note 6)		0.92	
	(Note 5)		271	
Thermal Resistance, Junction to Ambient	(Note 5)	R _{θJA}	136	°C/W
	(Note 6)		271	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

- Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1 inch square copper plate.
 7. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.

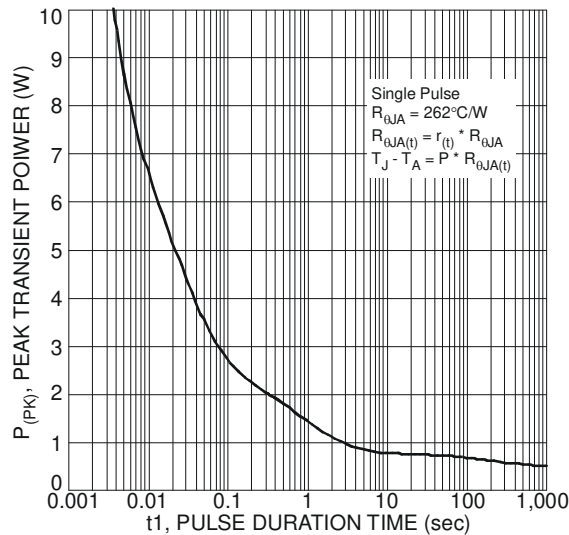


Fig. 1 Single Pulse Maximum Power Dissipation

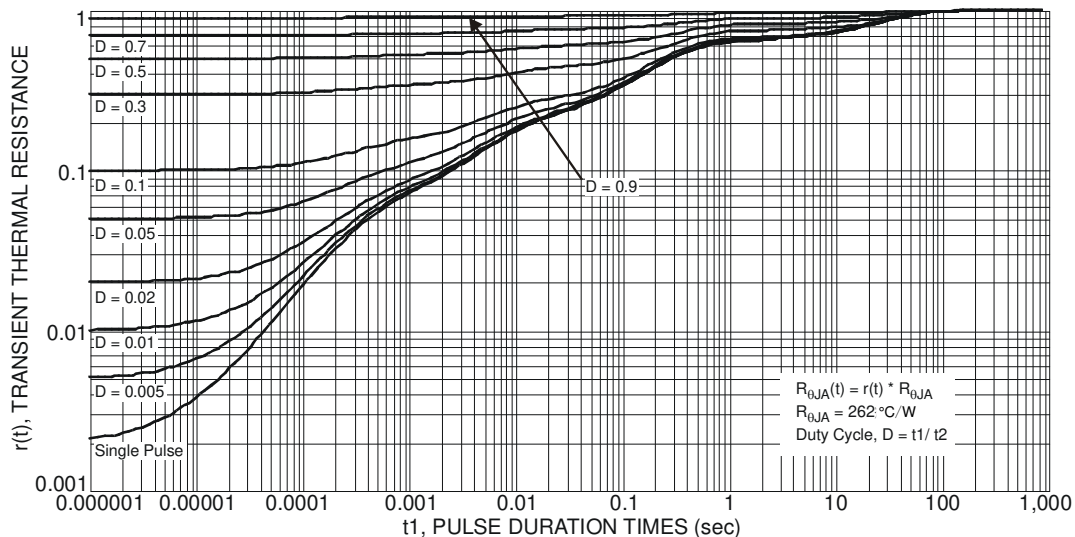
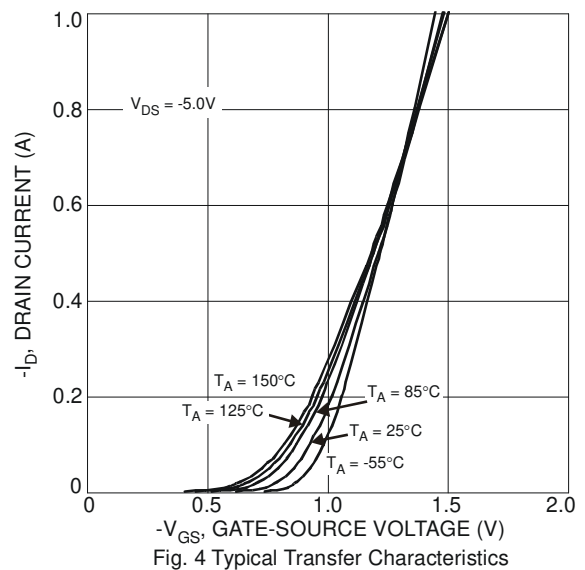
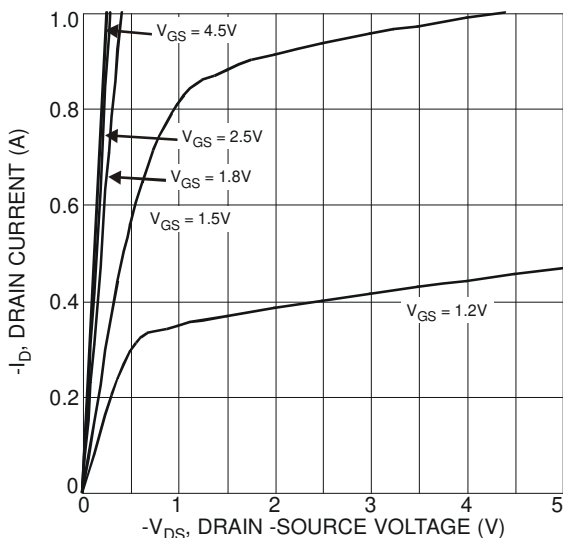


Fig. 2 Transient Thermal Resistance

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current $T_J = +25^\circ\text{C}$	I_{DSS}	-	-	-1	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	-	-	± 3	μA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.5	-0.6	-1.1	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	0.45	1	Ω	$V_{GS} = -4.5V, I_D = -400mA$
			0.54	1.5		$V_{GS} = -2.5V, I_D = -200mA$
			0.64	2		$V_{GS} = -1.8V, I_D = -100mA$
Forward Transfer Admittance	$ Y_{fs} $	50	-	-	mS	$V_{DS} = -3V, I_D = -300mA$
Diode Forward Voltage	V_{SD}	-	-	-1.2	V	$V_{GS} = 0V, I_S = -300mA$
DYNAMIC CHARACTERISTICS (Note9)						
Input Capacitance	C_{iss}	-	76	150	pF	$V_{DS} = -15V, V_{GS} = 0V,$ $f = 1.0MHz$
Output Capacitance	C_{oss}	-	9	20	pF	
Reverse Transfer Capacitance	C_{rss}	-	6.43	15	pF	
Gate Resistance	R_g	-	167	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge	Q_g	-	0.9	-	nC	$V_{GS} = -4.5V, V_{DS} = -15V, I_D = -1A$
Total Gate Charge	Q_g	-	1.5	-	nC	$V_{GS} = -8V, V_{DS} = -15V,$ $I_D = -1A$
Gate-Source Charge	Q_{gs}	-	0.1	-	nC	
Gate-Drain Charge	Q_{gd}	-	0.2	-	nC	
Turn-On Delay Time	$t_{D(ON)}$	-	4.98	-	ns	$V_{DD} = -10V, R_L = 10\Omega$ $V_{GS} = -4.5V, R_g = 6\Omega$
Turn-On Rise Time	t_R	-	5.85	-	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	-	35.7	-	ns	
Turn-Off Fall Time	t_F	-	16.6	-	ns	

Notes: 8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

Typical Electrical Characteristics


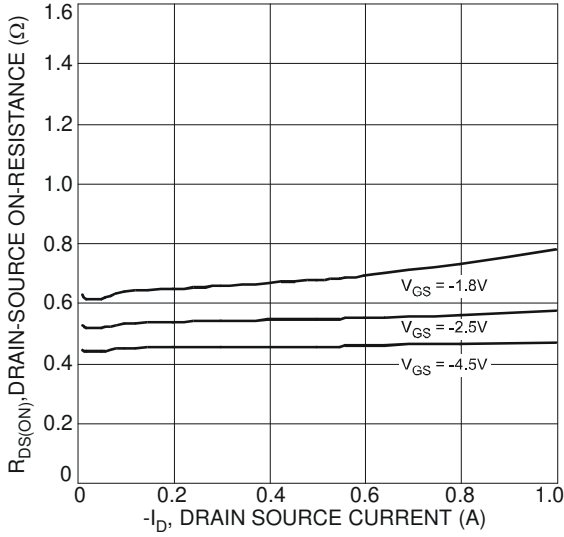


Fig. 5 Typical On-Resistance vs. Drain Current and Gate Voltage

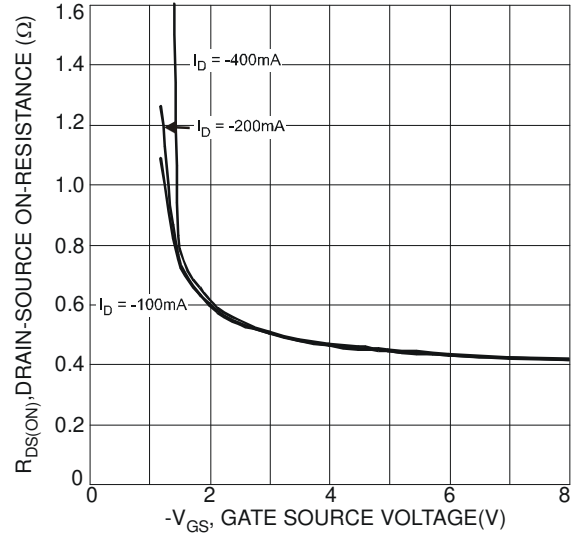


Fig. 6 Typical On-Resistance vs. Drain Current and Gate Voltage

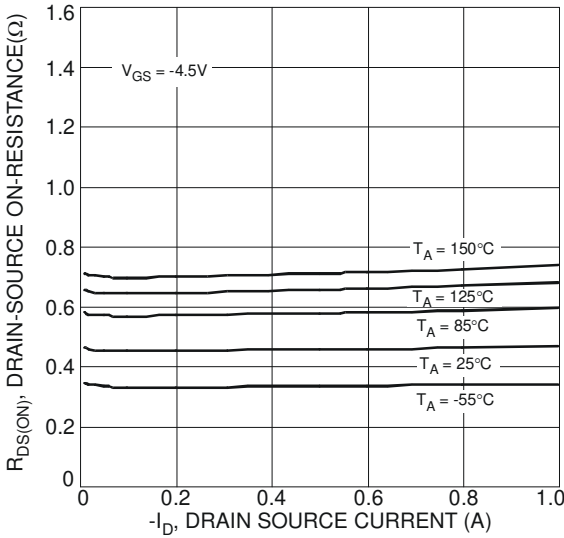


Fig. 7 Typical On-Resistance vs. Drain Current and Temperature

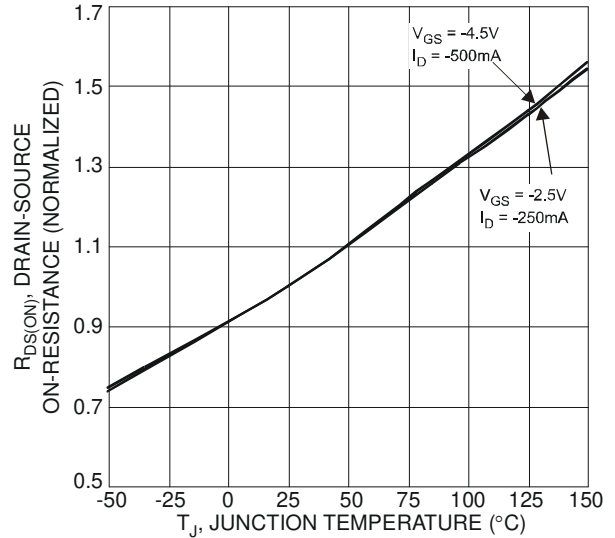


Fig. 8 On-Resistance Variation with Temperature

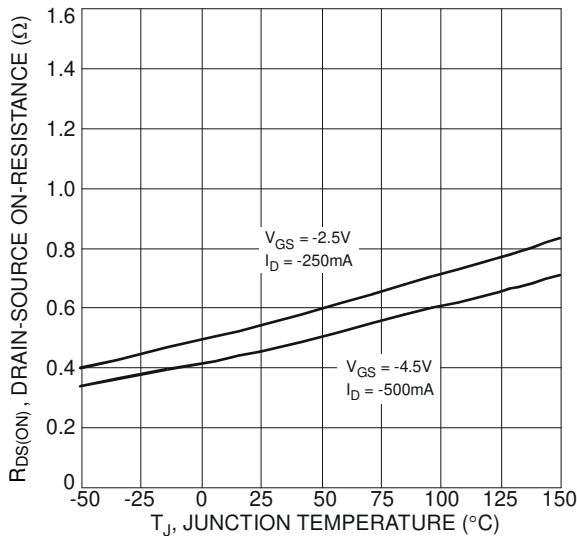


Fig. 9 On-Resistance Variation with Temperature

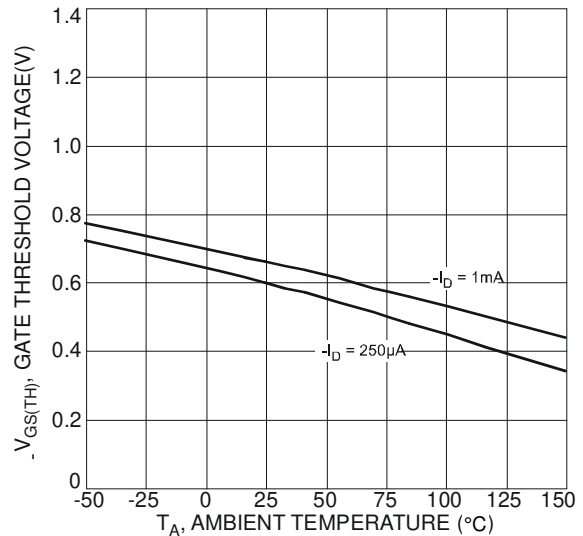


Fig. 10 Gate Threshold Variation vs. Ambient Temperature

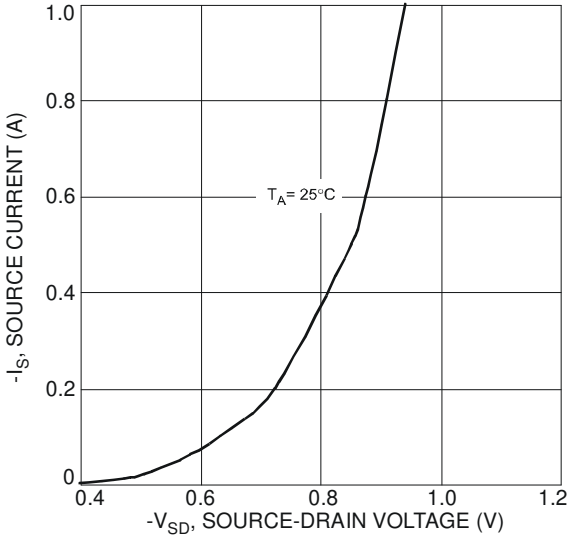


Fig. 11 Diode Forward Voltage vs. Current

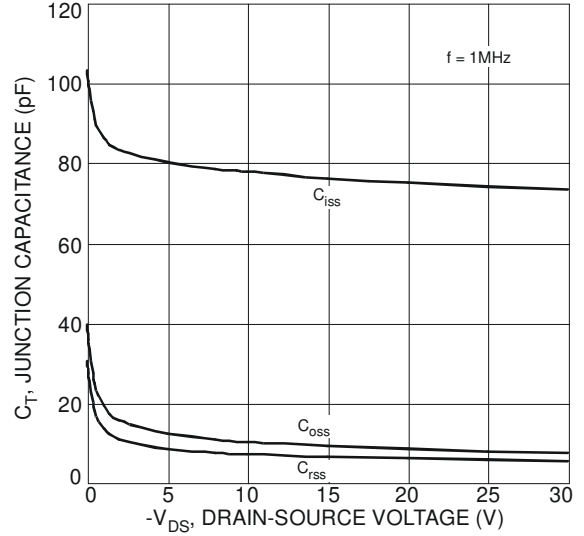


Fig. 12 Typical Junction Capacitance

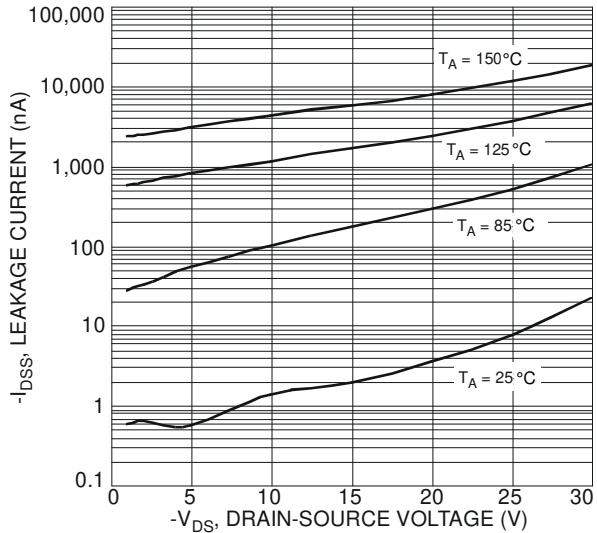


Fig. 13 Typical Drain-Source Leakage Current vs. Voltage

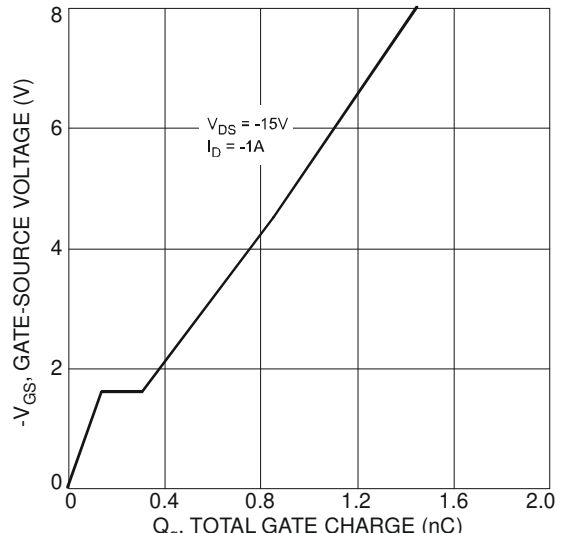
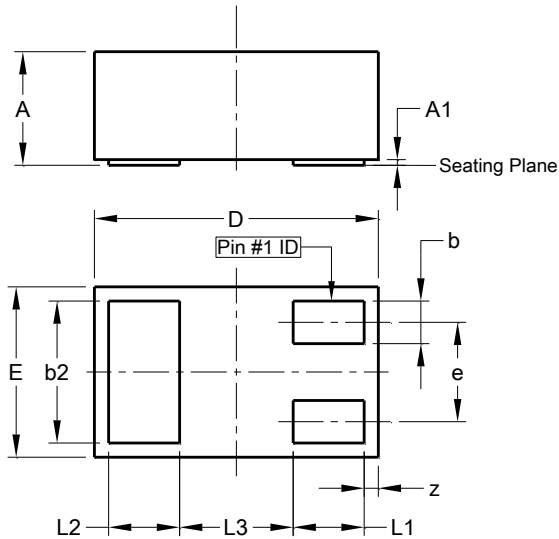


Fig. 14 Gate-Charge Characteristics

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-DFN1006-3

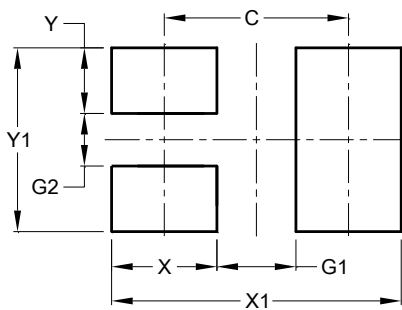


X2-DFN1006-3			
Dim	Min	Max	Typ
A		0.40	
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.05	1.00
E	0.55	0.65	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X2-DFN1006-3



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70

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